TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (π-MOSIII)

## 2SK2845

# Chopper Regulator, DC/DC Converter and Motor Drive Applications

 $\begin{array}{ll} \bullet & \text{Low drain-source ON-resistance} & : R_{DS \; (ON)} = 8.0 \; \Omega \; (typ.) \\ \bullet & \text{High forward transfer admittance} & : |Y_{fs}| = 0.9 \; S \; (typ.) \\ \bullet & \text{Low leakage current} & : I_{DSS} = 100 \; \mu\text{A} \; (max) \; (V_{DS} = 720 \; V) \\ \bullet & \text{Enhancement mode} & : V_{th} = 2.0 \; \text{to 4.0 V} \; (V_{DS} = 10 \; V, \; I_{D} = 1 \; \text{mA}) \\ \end{array}$ 

## Absolute Maximum Ratings (Ta = 25°C)

| Characteristic                         |                | Symbol           | Rating     | Unit |
|--|----------------|------------------|------------|------|
| Drain-source voltage                   |                | $V_{DSS}$        | 900        | V    |
| Drain-gate voltage ( $R_{GS}$ = 20 kΩ) |                | $V_{DGR}$        | 900        | V    |
| Gate-source voltage                    |                | $V_{GSS}$        | ±30        | V    |
| Drain current                          | DC (Note 1)    | I <sub>D</sub>   | 1          | Α    |
|  | Pulse (Note 1) | I <sub>DP</sub>  | 3          | A    |
| Drain power dissipation (Tc = 25°C)    |                | $P_{D}$          | 40         | W    |
| Single-pulse avalanche energy (Note 2) |                | E <sub>AS</sub>  | 324        | mJ   |
| Avalanche current                      |                | I <sub>AR</sub>  | 1          | Α    |
| Repetitive avalanche energy (Note 3)   |                | E <sub>AR</sub>  | 4.0        | mJ   |
| Channel temperature                    |                | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature range              |                | T <sub>stg</sub> | −55 to 150 | °C   |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

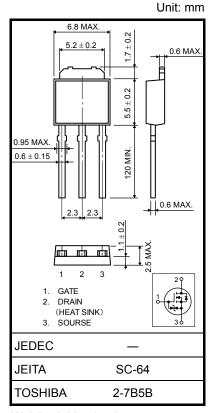
| Characteristic                         | Symbol                 | Max   | Unit |
|--|------------------------|-------|------|
| Thermal resistance, channel to case    | R <sub>th (ch-c)</sub> | 3.125 | °C/W |
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 125   | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

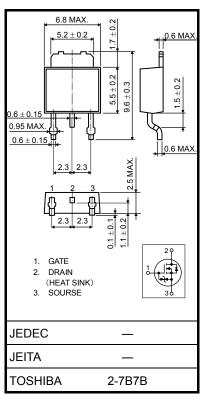
Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 594 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 1 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.36 g (typ.)



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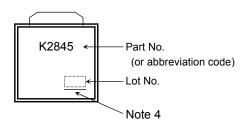
## **Electrical Characteristics (Ta = 25°C)**

| Charac  | cteristic       | Symbol               | Test Condition   | Min | Тур. | Max | Unit |
|---|-----------------|----------------------|--|-----|------|-----|------|
| Gate leakage cu                                 | rrent           | I <sub>GSS</sub>     | V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V                           |     | _    | ±10 | μΑ   |
| Gate-source bre                                 | akdown voltage  | V (BR) GSS           | I <sub>G</sub> = ±10 μA, V <sub>DS</sub> = 0 V                           | ±30 | _    | _   | V    |
| Drain cutoff curr                               | ent             | I <sub>DSS</sub>     | V <sub>DS</sub> = 720 V, V <sub>GS</sub> = 0 V                           | _   | _    | 100 | μA   |
| Drain-source bre                                | eakdown voltage | V (BR) DSS           | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V                            | 900 | _    | _   | V    |
| Gate threshold v                                | oltage          | $V_{th}$             | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA                            | 2.0 | _    | 4.0 | V    |
| Drain-source ON                                 | l-resistance    | R <sub>DS</sub> (ON) | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 A                           | _   | 8.0  | 9.0 | Ω    |
| Forward transfer                                | admittance      | Y <sub>fs</sub>      | V <sub>DS</sub> = 20 V, I <sub>D</sub> = 0.5 A                           |     | 0.9  | _   | S    |
| Input capacitano                                | e               | C <sub>iss</sub>     |  |     | 350  | _   | pF   |
| Reverse transfer capacitance                    |                 | C <sub>rss</sub>     | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz                 | _   | 8    | _   |      |
| Output capacitance                              |                 | Coss                 | ]  |     | 40   | _   |      |
| Switching time                                  | Rise time       | t <sub>r</sub>       | $V_{GS}$ $V_{OV}$ $V_{OUT}$ $V_{DD}$ $V_{DD}$ $V_{OUT}$ $V_{DD}$         | _   | 20   | _   | ns   |
|   | Turn-on time    | t <sub>on</sub>      |  | _   | 70   | _   |      |
|   | Fall time       | t <sub>f</sub>       |  | _   | 30   | _   |      |
|   | Turn-off time   | t <sub>off</sub>     | Duty $\leq 1\%$ , $t_{\mathbf{w}} = 10 \mu \mathbf{s}$                   | _   | 95   | _   |      |
| Total gate charge (gate-source plus gate-drain) |                 | Qg                   |  | _   | 15   | _   |      |
| Gate-source charge                              |                 | Q <sub>gs</sub>      | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}$ |     | 6    | _   | nC   |
| Gate-drain ("Miller") charge                    |                 | Q <sub>gd</sub>      |  |     | 9    | _   |      |

## **Source-Drain Ratings and Characteristics (Ta = 25°C)**

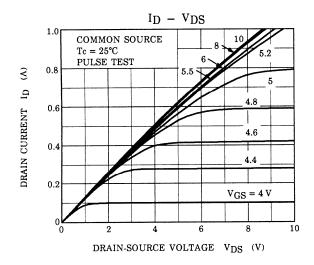
| Characteristic                            | Symbol           | Test Condition                               | Min | Тур. | Max  | Unit |
|---|------------------|--|-----|------|------|------|
| Continuous drain reverse current (Note 1) | I <sub>DR</sub>  | _  | _   | _    | 1    | Α    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub> | _  | _   | _    | 3    | Α    |
| Forward voltage (diode)                   | V <sub>DSF</sub> | I <sub>DR</sub> = 1 A, V <sub>GS</sub> = 0 V | _   | _    | -1.9 | V    |
| Reverse recovery time                     | t <sub>rr</sub>  | IDR = 1 A, VGS = 0 VdIDR / dt = 100 A / µs   | _   | 750  | -    | ns   |
| Reverse recovery charge                   | Q <sub>rr</sub>  | TIDR - TA, VGS - 0 VαΙDR / αι - 100 Α / μs   |     | 3    | -    | μC   |

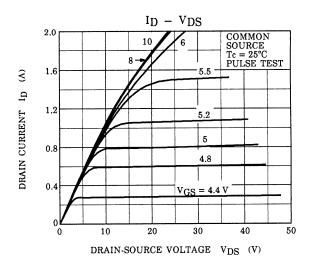
## Marking

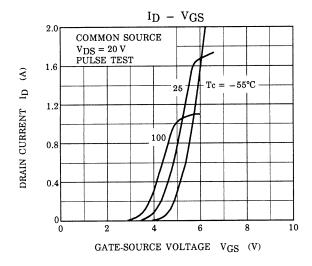


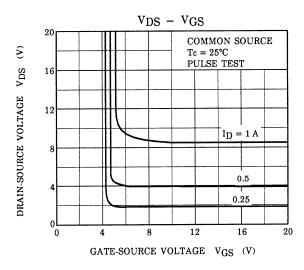
Note 4 : A line under a Lot No. identifies the indication of product Labels [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

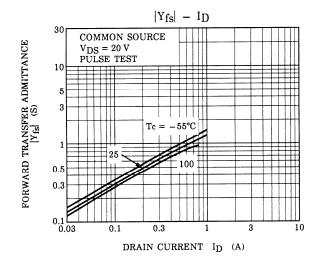
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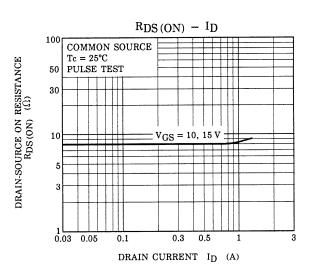




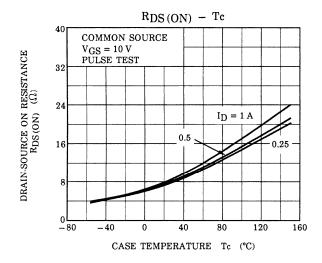


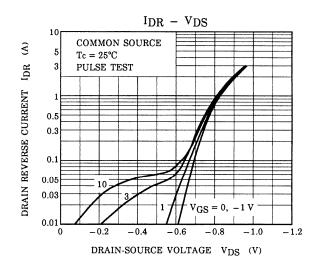


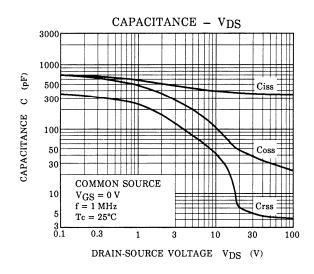


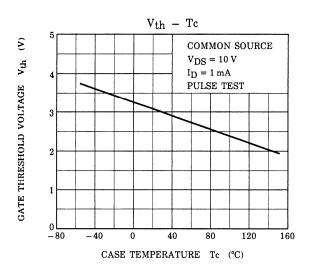


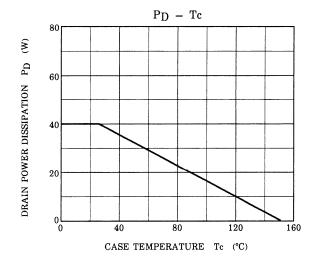
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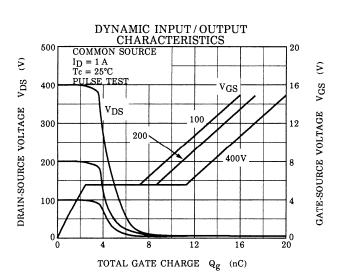


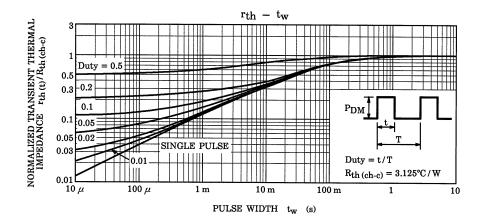


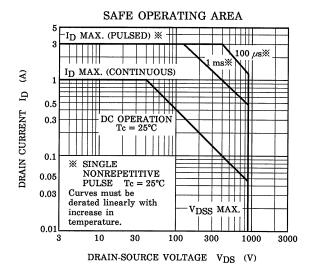


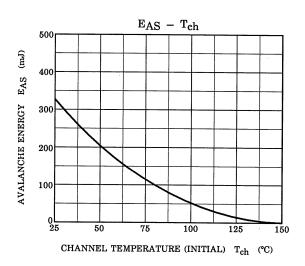


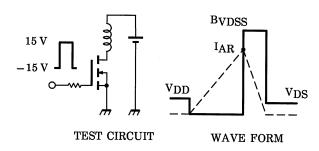












$$\begin{aligned} R_G &= 25~\Omega \\ V_{DD} &= 90~V,~L = 594~mH \end{aligned} \qquad EAS &= \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right) \end{aligned}$$

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